Digital Transistors (BRT) R1 = 4.7 k Ω , R2 = 47 k Ω

NPN Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

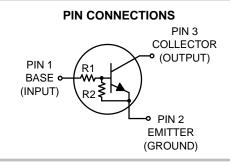
Rating	Symbol	Max	Unit
Collector-Base Voltage	V _{CBO}	50	Vdc
Collector-Emitter Voltage	V _{CEO}	50	Vdc
Collector Current – Continuous	۱ _C	100	mAdc
Input Forward Voltage	V _{IN(fwd)}	30	Vdc
Input Reverse Voltage	V _{IN(rev)}	5	Vdc

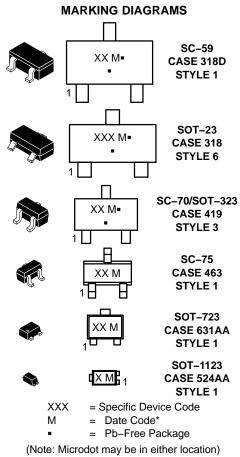
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.



ON Semiconductor®

www.onsemi.com





*Date Code orientation may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

1

Table 1. ORDERING INFORMATION

Device	Part Marking	Package	Shipping [†]
MUN2233T1G, NSVMUN2233T1G*	8K	SC–59 (Pb–Free)	3000 / Tape & Reel
MMUN2233LT1G, SMMUN2233LT1G*	A8K	SOT-23 (Pb-Free)	3000 / Tape & Reel
NSVMMUN2233LT3G*	A8K	SOT-23 (Pb-Free)	10000 / Tape & Reel
MUN5233T1G, SMUN5233T1G*	8K	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTC143ZET1G, NSVDTC143ZET1G*	8K	SC–75 (Pb–Free)	3000 / Tape & Reel
DTC143ZM3T5G, NSVDTC143ZM3T5G*	8K	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBC143ZF3T5G	R	SOT-1123 (Pb-Free)	8000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

(1) SC-75 and SC-70/SOT-323; Minimum Pad

(4) SOT-1123; 100 mm², 1 oz. copper trace

(2) SC–59; Minimum Pad (3) SOT–23; Minimum Pad

(5) SOT-723; Minimum Pad

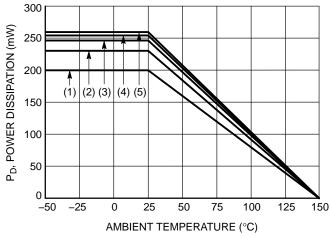


Figure 1. Derating Curve

Table 2. THERMAL CHARACTERISTICS

Characteristic		Symbol	Max	Unit
THERMAL CHARACTERISTICS (SC-59) (MUN2233)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1) (Note 2)	P _D	230 338	mW
Derate above 25°C	(Note 1) (Note 2)		1.8 2.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	540 370	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ ext{ heta}JL}$	264 287	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-23) (MMUN2233L)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1)	P _D	246 400 2.0	mW
	(Note 2)		3.2	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	508 311	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ extsf{ heta}JL}$	174 208	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-70/SOT-323) (MUN5233)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1)	PD	202	mW
Derate above 25°C	(Note 2) (Note 1) (Note 2)		310 1.6 2.5	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	618 403	°C/W
Thermal Resistance, Junction to Lead	(Note 1) (Note 2)	$R_{ ext{ heta}JL}$	280 332	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SC-75) (DTC143ZE)				
Total Device Dissipation $T_A = 25^{\circ}C$	(Note 1) (Note 2)	PD	200 300	mW
Derate above 25°C	(Note 1) (Note 2)		1.6 2.4	mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	600 400	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C
THERMAL CHARACTERISTICS (SOT-723) (DTC143ZM3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above 25°C	(Note 1) (Note 2) (Note 1)	PD	260 600 2.0	mW mW/°C
Derait above 23 C	(Note 1) (Note 2)		2.0 4.8	
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	R_{\thetaJA}	480 205	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

2. FR-4 @ 1.0 x 1.0 Inch Pad.

3. FR – 4 @ 100 mm², 1 oz. copper traces, still air. 4. FR – 4 @ 500 mm², 1 oz. copper traces, still air.

Table 2. THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
THERMAL CHARACTERISTICS (SOT-1123) (NSBC143ZF3)				
Total Device Dissipation $T_A = 25^{\circ}C$ Derate above $25^{\circ}C$	(Note 3) (Note 4) (Note 3) (Note 4)	P _D	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 3) (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead	(Note 3)	$R_{ ext{ heta}JL}$	193	°C/W
Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

1. FR-4 @ Minimum Pad.

2. FR-4 @ 1.0 x 1.0 Inch Pad.

3. FR $-4 @ 100 \text{ mm}^2$, 1 oz. copper traces, still air. 4. FR $-4 @ 500 \text{ mm}^2$, 1 oz. copper traces, still air.

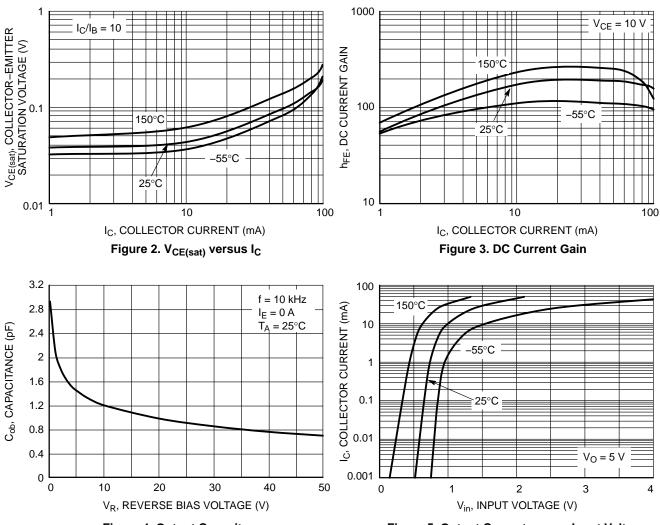
Table 3. ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS			•		
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I _{СВО}	_	-	100	nAdc
Collector–Emitter Cutoff Current ($V_{CE} = 50 \text{ V}, I_B = 0$)	ICEO	-	-	500	nAdc
Emitter–Base Cutoff Current ($V_{EB} = 6.0 \text{ V}, I_C = 0$)	I _{EBO}	_	-	0.18	mAdc
Collector–Base Breakdown Voltage $(I_C = 10 \ \mu\text{A}, I_E = 0)$	V _{(BR)CBO}	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) $(I_C = 2.0 \text{ mA}, I_B = 0)$	V _{(BR)CEO}	50	_	_	Vdc
ON CHARACTERISTICS			-	-	-
DC Current Gain (Note 5) ($I_C = 5.0 \text{ mA}, V_{CE} = 10 \text{ V}$)	h _{FE}	80	200	_	
Collector – Emitter Saturation Voltage (Note 5) $(I_{C} = 10 \text{ mA}, I_{B} = 1.0 \text{ mA})$	VCE(sat)	_	_	0.25	Vdc
Input Voltage (off) $(V_{CE} = 5.0 \text{ V}, I_C = 100 \mu\text{A})$	V _{i(off)}	_	0.6	0.5	Vdc
Input Voltage (on) ($V_{CE} = 0.3 \text{ V}, I_C = 5 \text{ mA}$)	V _{i(on)}	1.3	0.9	-	Vdc
Output Voltage (on) (V _{CC} = 5.0 V, V _B = 2.5 V, R _L = 1.0 k Ω)	V _{OL}	_	_	0.2	Vdc
Output Voltage (off) (V _{CC} = 5.0 V, V _B = 0.5 V, R _L = 1.0 k Ω)	V _{OH}	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R ₁ /R ₂	0.08	0.1	0.12	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle $\leq 2\%$.

www.onsemi.com 4



TYPICAL CHARACTERISTICS MUN2233, MMUN2233L, MUN5233, DTC143ZE, DTC143ZM3

Figure 4. Output Capacitance

Figure 5. Output Current versus Input Voltage

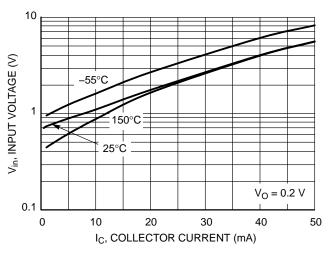
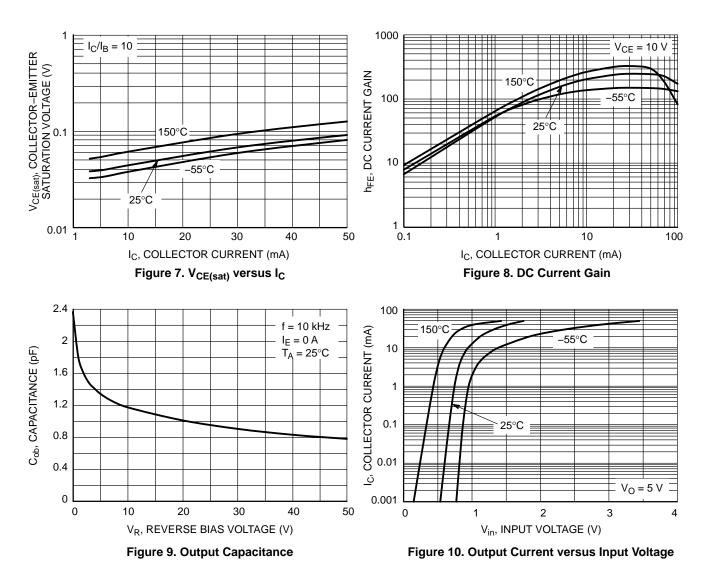


Figure 6. Input Voltage versus Output Current



TYPICAL CHARACTERISTICS NSBC143ZF3

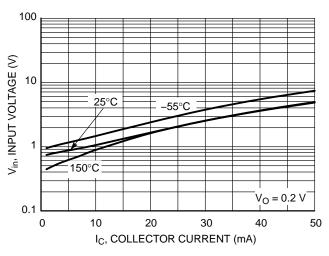


Figure 11. Input Voltage versus Output Current

<u>www.onsemi.com</u> 6

n

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

onsemi



SCALE 4:1

A____ ' A1SOT-23 (TO-236) CASE 318 ISSUE AT

0.25

-1.1

DETAIL A

END VIEW

DATE 01 MAR 2023

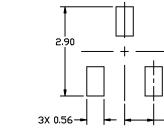
3X -0.95

0.95

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS				INCHES	
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η _E	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



PITCH RECOMMENDED MOUNTING FOOTPRINT

* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

GENERIC MARKING DIAGRAM*



XXX = Specific Device Code

M = Date Code

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Report Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 1 OF 2
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.			

© Semiconductor Components Industries, LLC, 2019

MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

onsemi

SOT-23 (TO-236) CASE 318 ISSUE AT

DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	I.	
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

DOCUMENT NUMBER:	98ASB42226B Electronic versions are uncontrolled except when accessed directly from the Document Repos Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-23 (TO-236)		PAGE 2 OF 2

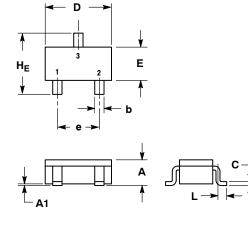
onsemi and ONSEMI: are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

DURSEM



SC-59 CASE 318D-04 **ISSUE H**

DATE 28 JUN 2012



GENERIC **MARKING DIAGRAM***



XXX	= Specific Device Code
М	= Date Code
	= Pb-Free Package*

= Pb-Free Package*

(*Note: Microdot may be in either location)

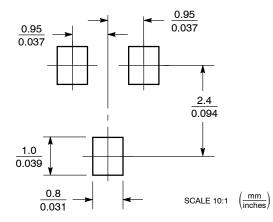
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

NOTES:

DIRES:
DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
CONTROLLING DIMENSION: MILLIMETER.

	м	MILLIMETERS			INCHES	
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	1.00	1.15	1.30	0.039	0.045	0.051
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.35	0.43	0.50	0.014	0.017	0.020
c	0.09	0.14	0.18	0.003	0.005	0.007
D	2.70	2.90	3.10	0.106	0.114	0.122
Е	1.30	1.50	1.70	0.051	0.059	0.067
е	1.70	1.90	2.10	0.067	0.075	0.083
L	0.20	0.40	0.60	0.008	0.016	0.024
HE	2.50	2.80	3.00	0.099	0.110	0.118



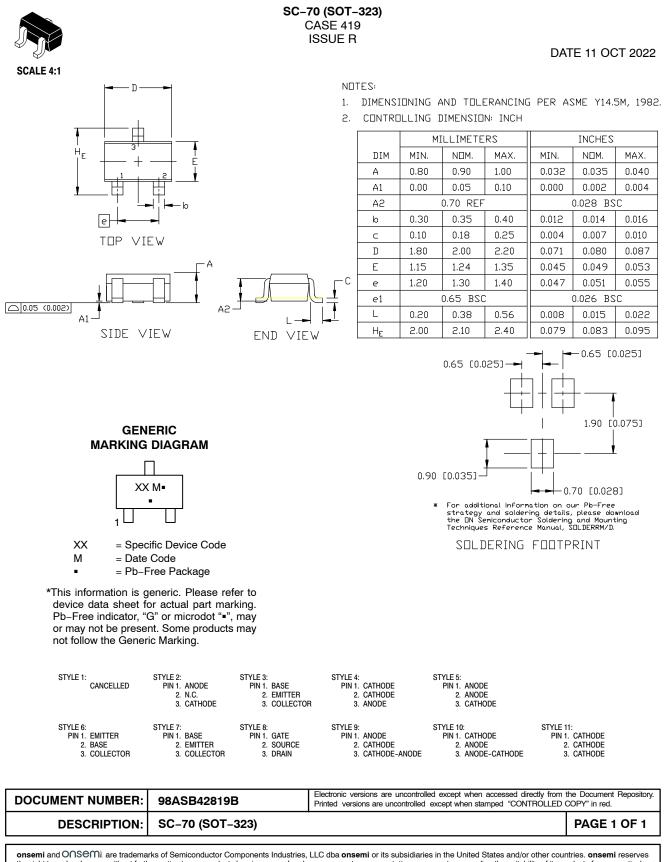


*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

STYLE 1:	STYLE 2:	STYLE 3:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE
2. EMITTER	2. N.C.	2. ANODE
COLLECTOR	CATHODE	3. CATHODE
STYLE 4: PIN 1. CATHODE 2. N.C. 3. ANODE	STYLE 5: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 6: PIN 1. ANODE 2. CATHODE 3. ANODE/CATHODE

DOCUMENT NUMBER:	98ASB42664B Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SC-59		PAGE 1 OF 1	
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.				

onsemi



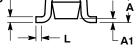
the right to make charges without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights of theres.

DUSEM

DATE 07 AUG 2015



ISSUE G SCALE 4:1 -E--De ¥ b 3 PL 🕀 0.20 (0.008) 🛞 D H_{E} 0.20 (0.008) E _ С



STYLE 1: PIN 1. BASE 2. EMITTER 3. COLLECTOR



STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

SC-75/SOT-416 **CASE 463**

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

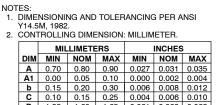
STYLE 5: PIN 1. GATE 2 SOURCE 3. DRAIN

GENERIC **MARKING DIAGRAM***



- XX = Specific Device Code
- Μ = Date Code
- = Pb-Free Package

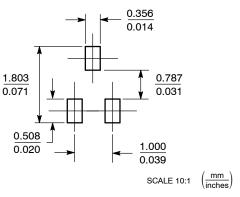
*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



D 1.55 1.60 1.65 0.061 0.063 0.065 E 0.70 0.80 0.90 0.027 0.031 0.035 0.04 BSC
 e
 1.00 BSC
 0.04 BSC

 L
 0.10
 0.15
 0.20
 0.004
 0.006
 0.008
 H_E 1.50 1.60 1.70 0.060 0.063 0.067

RECOMMENDED **SOLDERING FOOTPRINT***



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

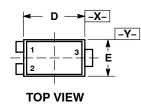
DOCUMENT NUMBER:	98ASB15184C Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
DESCRIPTION:	SC-75/SOT-416		PAGE 1 OF 1	
onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves				

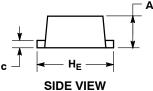
the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

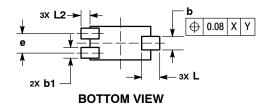
DUSem



SCALE 8:1







SOT-1123 CASE 524AA **ISSUE C**

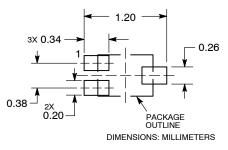
DATE 29 NOV 2011

NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME

- University of the second state of
- MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	MAX	
Α	0.34	0.40	
b	0.15	0.28	
b1	0.10	0.20	
с	0.07	0.17	
D	0.75	0.85	
Е	0.55	0.65	
е	0.35 0.40		
HE	0.95 1.05		
Ĺ	0.185 REF		
L2	0.05	0.15	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC **MARKING DIAGRAM***



= Specific Device Code Х Μ = Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. C
2. EMITTER	2. N/C	2. ANODE	2. C
3. COLLECTOR	3. CATHODE	3. CATHODE	3. A

. CATHODE CATHODE ANODE

STYLE 5: PIN 1. GATE 2. SOURCE 3. DRAIN

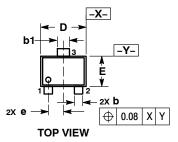
DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-1123, 3-LEAD, 1.0x0.6x0.37, 0.35P		PAGE 1 OF 1	
onsemi and ONSEMi are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.				

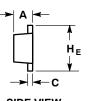
DUDSem

DATE 10 AUG 2009



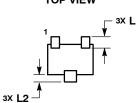
SCALE 4:1





SOT-723 CASE 631AA **ISSUE D**

SIDE VIEW

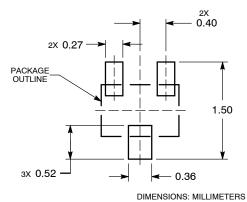


BOTTOM VIEW

- NOTES: 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. 2. CONTROLLING DIMENSION: MILLIMETERS. 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL. 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

	MILLIMETERS		
DIM	MIN	NOM	MAX
Α	0.45	0.50	0.55
b	0.15	0.21	0.27
b1	0.25	0.31	0.37
С	0.07	0.12	0.17
D	1.15	1.20	1.25
Е	0.75	0.80	0.85
е		0.40 BSC)
ΗE	1.15	1.20	1.25
Г	0.29 REF		
L2	0.15	0.20	0.25

RECOMMENDED **SOLDERING FOOTPRINT***



Techniques Reference Manual, SOLDERRM/D.

*For additional information on our Pb-Free strategy and soldering details, please download the **onsemi** Soldering and Mounting

GENERIC **MARKING DIAGRAM***



XX	= Specific Device Code
М	= Date Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:	STYLE 2:	STYLE 3:	STYLE 4:	STYLE 5:
PIN 1. BASE	PIN 1. ANODE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. GATE
2. EMITTER	2. N/C	2. ANODE	2. CATHODE	2. SOURCE
3. COLLECTOR	3. CATHODE	3. CATHODE	3. ANODE	3. DRAIN

DOCUMENT NUMBER:	98AON12989D	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SOT-723		PAGE 1 OF 1	
onsemi and ONSEMI. are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.				

© Semiconductor Components Industries, LLC, 2023

onsemi, ONSEMI, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "onsemi" or its affiliates and/or subsidiaries in the United States and/or other countries. onsemi owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of onsemi's product/patent coverage may be accessed at <u>www.onsemi.com/site/pdf/Patent-Marking.pdf</u>. onsemi reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and onsemi makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using onsemi products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by onsemi. "Typical" parameters which may be provided in onsemi data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. onsemi does not convey any license under any of its intellectual property rights or the rights of others. onsemi products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use onsemi products for any such u

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales 单击下面可查看定价,库存,交付和生命周期等信息

>>ON Semiconductor(安森美)